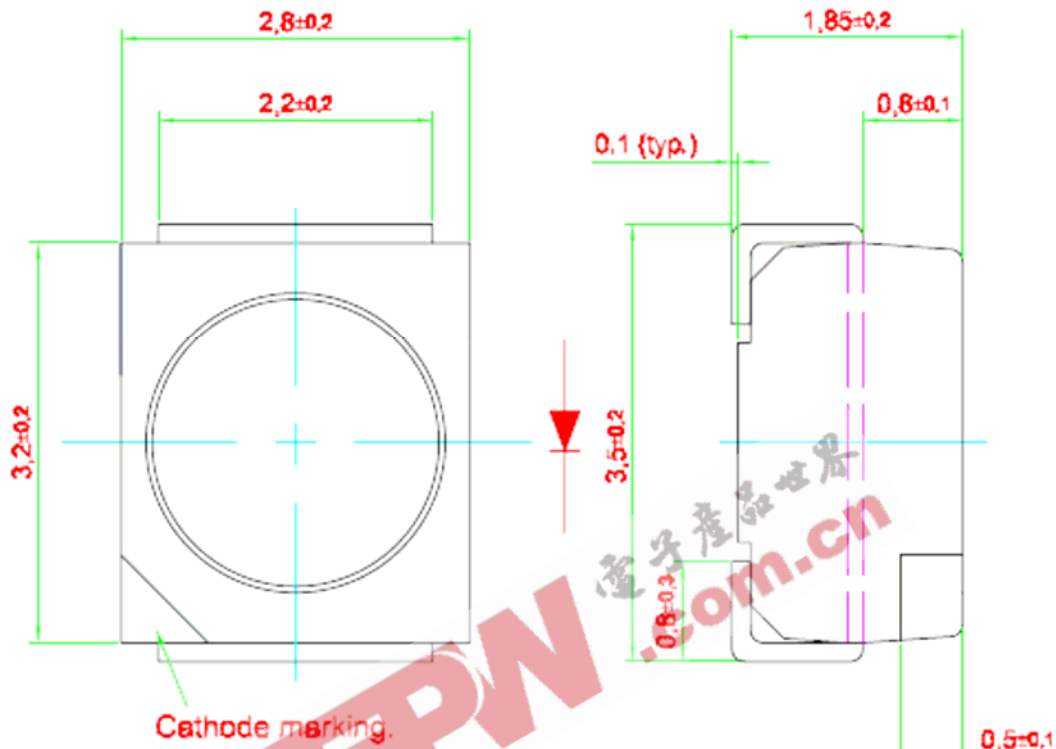


DomiLED – GaP : DDx-GJS-I1



- Low current surface mount LED.
- 120° viewing angle.
- Small package outline (LxWxH) of 3.2 x 2.8 x 1.8 mm.
- Qualified according to JEDEC moisture sensitivity Level 2.
- Compatible to both IR reflow soldering and TTW soldering.

Part Ordering Number	Chip Technology / Color	Luminous Intensity @ If = 10mA lv (mcd)
DDR-GJS-J2L1-1-I1 <ul style="list-style-type: none"> • DDR-GJS-J2 • DDR-GJS-K1 • DDR-GJS-K2 • DDR-GJS-L1 	GaP / Red, 625 nm	5.6 ... 14.0 5.6 ... 7.2 7.2 ... 9.0 9.0 ... 11.2 11.2 ... 14.0
DDO-GJS-H2K1-1-I1 <ul style="list-style-type: none"> • DDO-GJS-H2 • DDO-GJS-J1 • DDO-GJS-J2 • DDO-GJS-K1 	GaP / Orange, 605 nm	3.55 ... 9.0 3.55 ... 4.5 4.5 ... 5.6 5.6 ... 7.2 7.2 ... 9.0
DDY-GJS- H2K1-1-I1 <ul style="list-style-type: none"> • DDY-GJS-H2 • DDY-GJS-J1 • DDY-GJS-J2 • DDY-GJS-K1 	GaP / Yellow, 587 nm	3.55 ... 9.0 3.55 ... 4.5 4.5 ... 5.6 5.6 ... 7.2 7.2 ... 9.0
DDG-GJS- KL2-1-I1 <ul style="list-style-type: none"> • DDG-GJS-K1 • DDG-GJS-K2 • DDG-GJS-L1 • DDG-GJS-L2 	GaP / Green, 570 nm	7.2 ... 18.0 7.2 ... 9.0 9.0 ... 11.2 11.2 ... 14.0 14.0 ... 18.0
DDP-GJS-GH2-1-I1 <ul style="list-style-type: none"> • DDP-GJS-G1 • DDP-GJS-G2 • DDP-GJS-H1 • DDP-GJS-H2 	GaP / Green, 560 nm	1.80 ... 4.50 1.80 ... 2.24 2.24 ... 2.80 2.80 ... 3.55 3.55 ... 4.50

NOTE:

1. All part number above comes in a quantity of 2000 units per reel.
2. Luminous intensity is measured with an accuracy of $\pm 11\%$.
3. Wavelength binning is carried for all units as per the wavelength-binning table. Only one wavelength group is allowed for each reel.

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Characteristics.

Forward voltage @ $I_f=10$ mA.	Chip Type	Viewing angle at 50% I_v	Max reverse current, I_R @ $V_R = 5V$.
2.05 V (typ.); 2.45 V (max)	GaP	120°	100 μA

All forward voltages are measured using a current pulse of 1 ms and has an accuracy of ± 0.1 V.

Wavelength Grouping.

Color	Group	Wavelength distribution (nm)
DDR; Red	Full	620 – 635
	W	600 – 612
DDO; Orange	W	600 - 603
	X	603 - 606
	Y	606 - 609
	Z	609 - 612
	Full	620 – 635
DDY; Yellow	Full	582 – 594
	W	582 – 585
	X	585 – 588
	Y	588 - 591
	Z	591 - 594
DDG; Green	Full	564.5 – 576.5
	W	564.5 – 567.5
	X	567.5 – 570.5
	Y	570.5 – 573.5
	Z	573.5 – 576.5
DDP; Pure Green	Full	552.5 – 564.5
	W	552.5 – 555.5
	X	555.5 – 558.5
	Y	558.5 – 561.5
	Z	561.5 – 564.5

Dominant wavelength is measured with an accuracy of ± 1 nm.

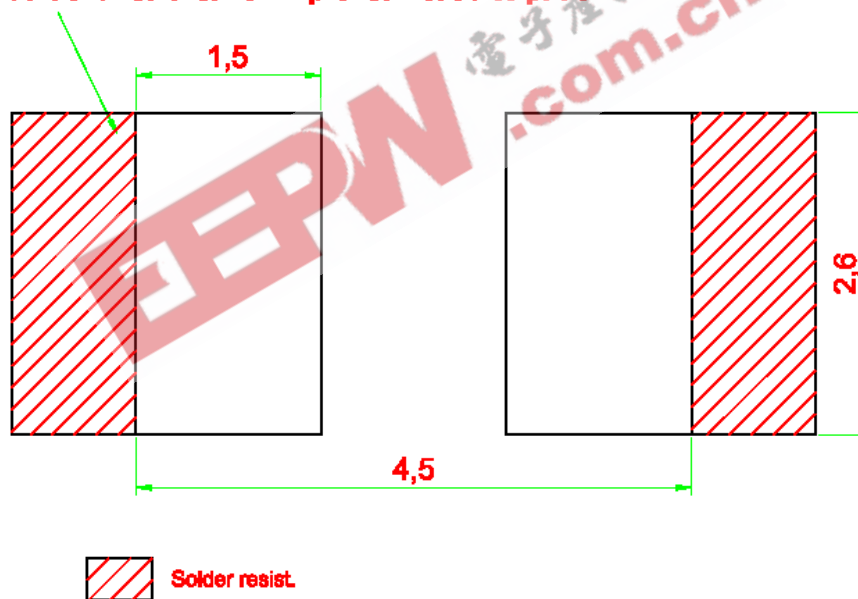
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Absolute Maximum Ratings.

	Maximum Value	Unit
DC forward current.	30	mA
Peak pulse current; ($t_p \leq 10 \mu\text{s}$, Duty cycle = 0.005)	500	mA
Reverse voltage.	5	V
LED junction temperature.	100	°C
Operating temperature.	-40 ... +100	°C
Storage temperature.	-40 ... +100	°C
Power dissipation (at room temperature)	75	mW

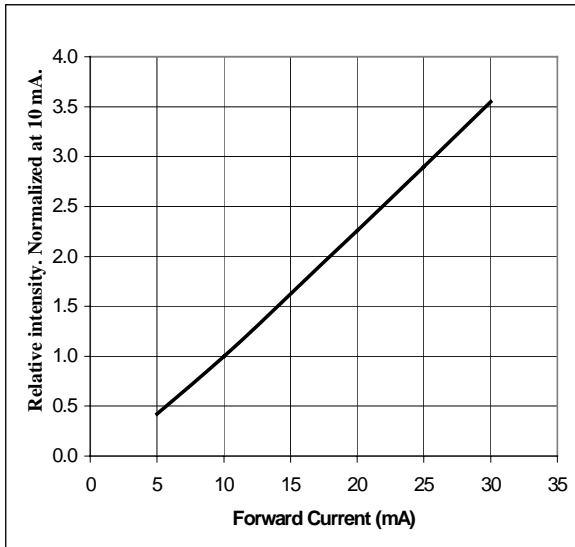
Recommended Solder Pad

Additional Cu area for improved heat dissipation.

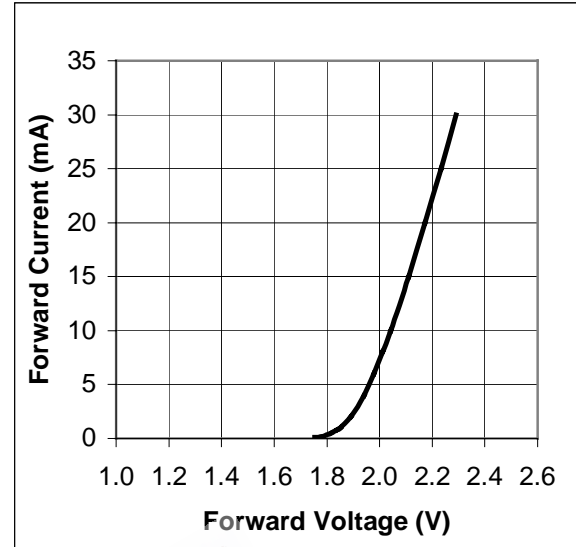


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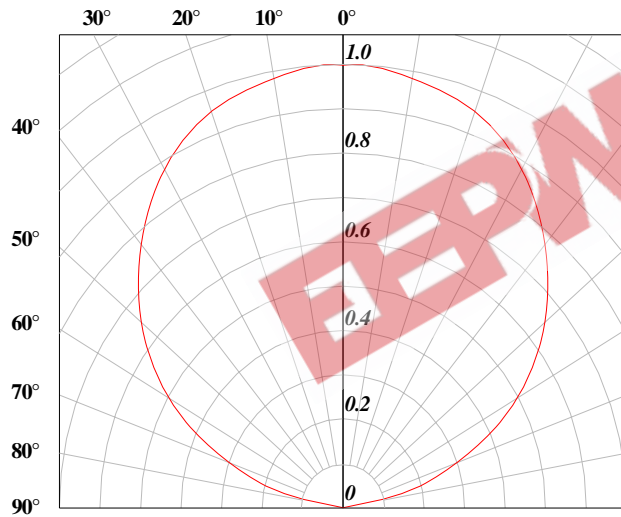
Relative luminous intensity vs. forward current.



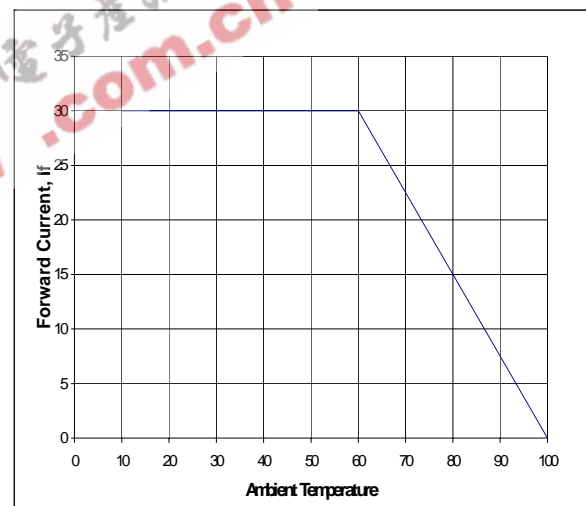
Forward current vs. forward voltage.



Radiation pattern.



Maximum forward current vs. temperature.

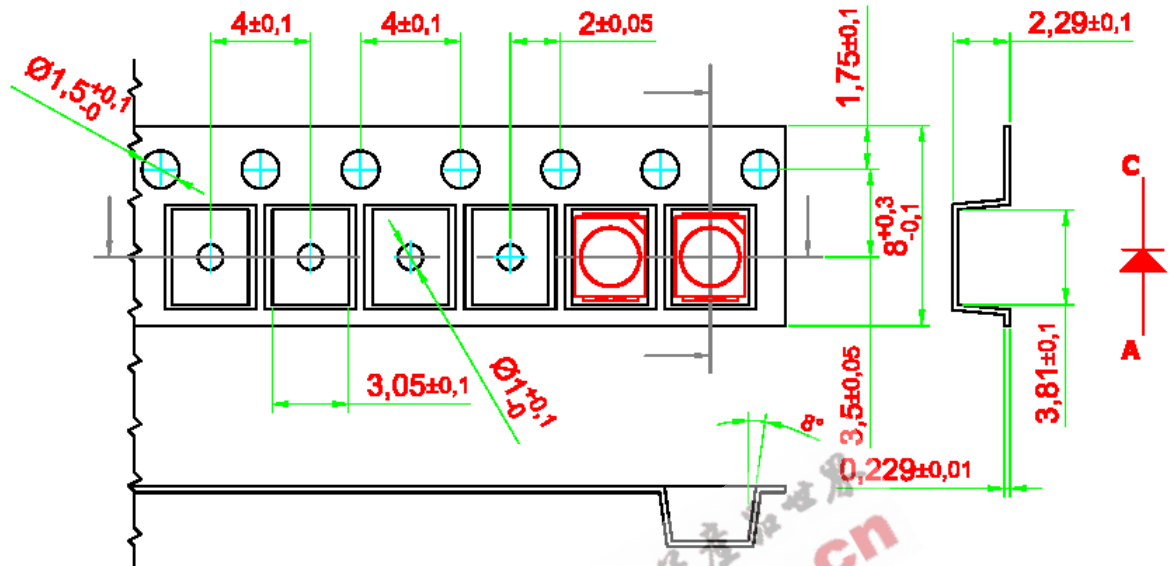


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Taping And Orientation.

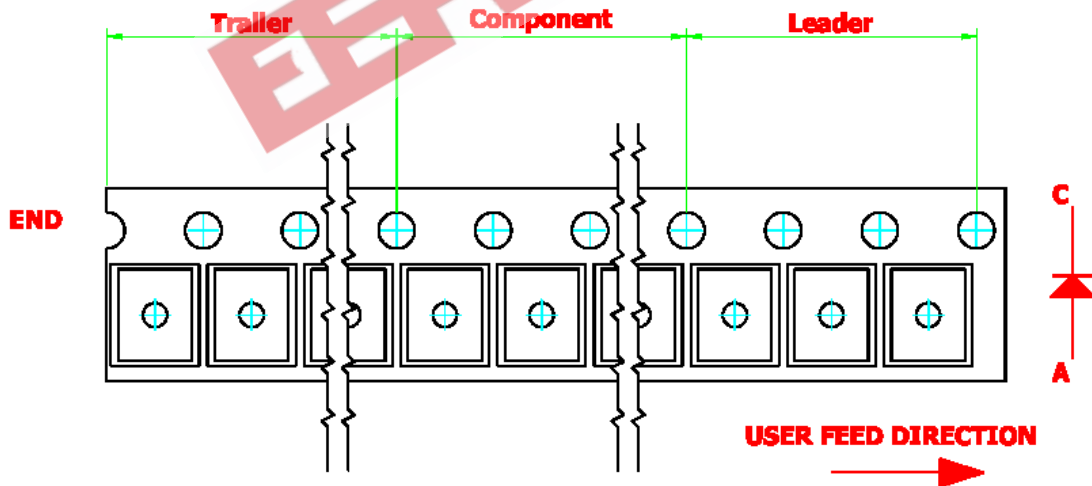
Reels come in quantity of 2000 units.

Reel diameter is 180 mm .

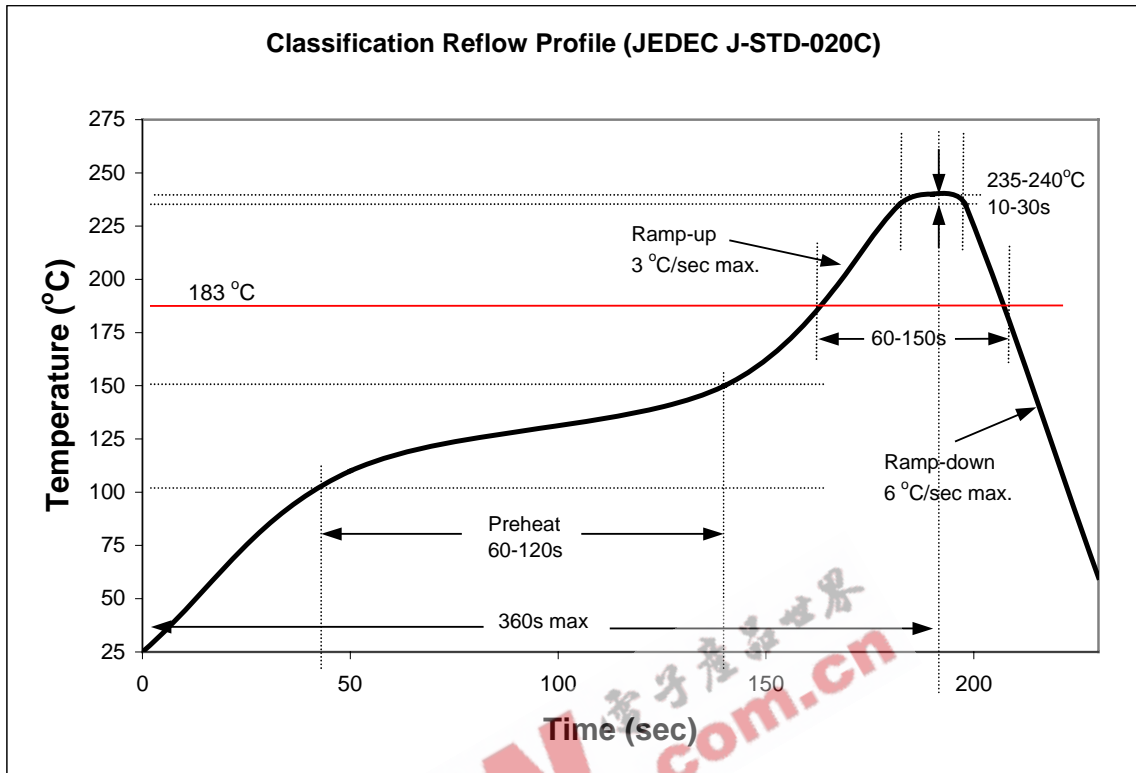


200 mm min. for $\varnothing 180$ reel.
200 mm min. for $\varnothing 330$ reel.

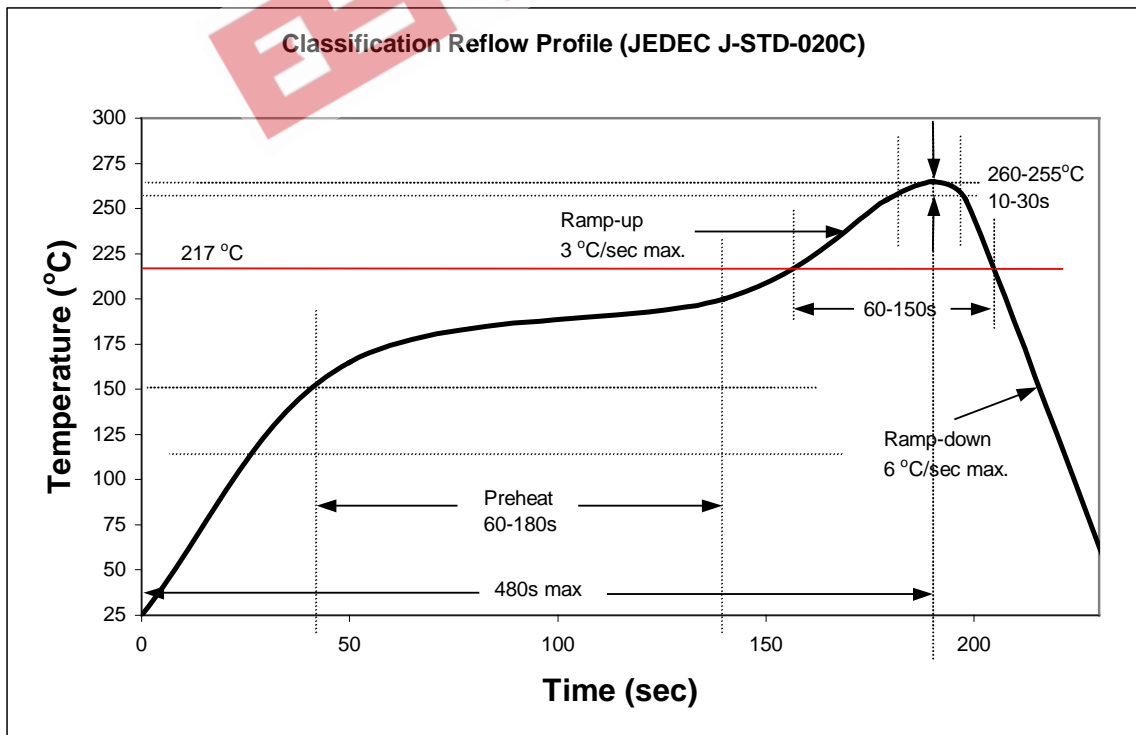
480 mm min. for $\varnothing 180$ reel.
960 mm min. for $\varnothing 330$ reel.



Recommended Sn-Pb IR-Reflow Soldering Profile.



Recommended Pb Free IR-Reflow Soldering Profile.



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